

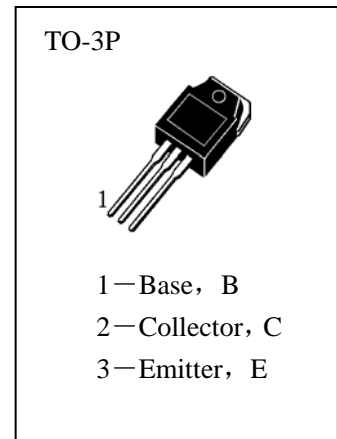


■ APPLICATIONS

- Power Amplifier Applications.
- Complementary to HA1962.

■ ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

T_{stg}—Storage Temperature..... -65~150°C
 T_j—Junction Temperature..... 150°C
 P_C—Collector Dissipation (T_c=25°C) 130W
 V_{CB0}—Collector-Base Voltage..... 230V
 V_{CEO}—Collector-Emitter Voltage..... 230V
 V_{EBO}—Emitter-Base Voltage..... 5V
 I_C—Collector Current (DC) 15A
 I_{CP}—Collector Current (Pulse) 30A
 I_b—Base Current..... 1.5A



■ ELECTRICAL CHARACTERISTICS (T_a=25°C)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV _{CB0}	Collector-Base Breakdown Voltage	230			V	I _C =100 μ A, I _E =0
BV _{CEO}	Collector-Emitter Breakdown Voltage	230			V	I _C =50mA, I _B =0
BV _{EBO}	Emitter-Base Breakdown Voltage	5			V	I _E =100 μ A, I _C =0
I _{CBO}	Collector Cut-off Current			5	μ A	V _{CB} =230V, I _E =0
I _{EBO}	Emitter Cut-off Current			5	μ A	V _{EB} =5V, I _C =0
H _{FE} (1)	DC Current Gain	55		160		V _{CE} =5V, I _C =1A
H _{FE} (2)	DC Current Gain	35				V _{CE} =5V, I _C =7A
V _{CE(sat)}	Collector- Emitter Saturation Voltage		0.4	3	V	I _C =8A, I _B =0.8A
V _{BE}	Base-Emitter Voltage			1.5	V	V _{CE} =5V, I _C =7A
f _T	Current Gain-Bandwidth Product		30		MHz	V _{CE} =5V, I _C =1A
C _{ob}	Output Capacitance		200		pF	V _{CB} =10V, I _E =0, f=1MHz

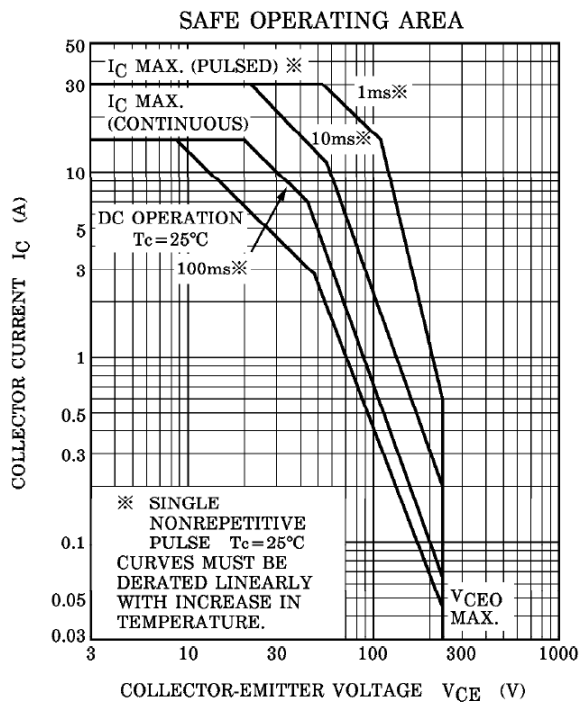
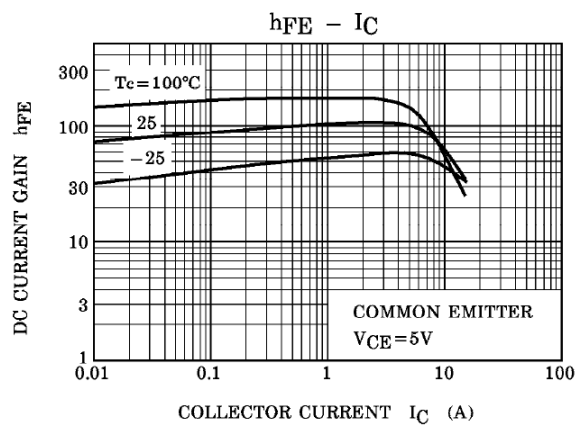
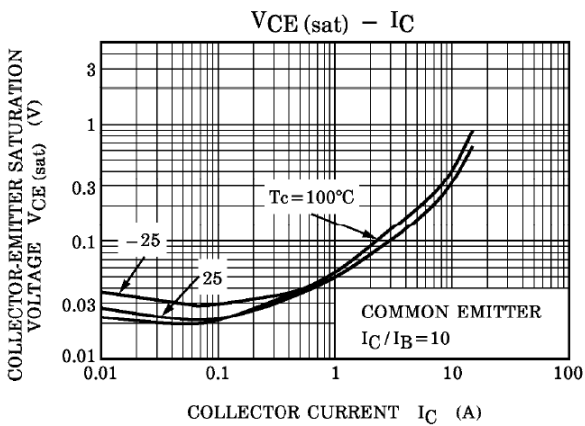
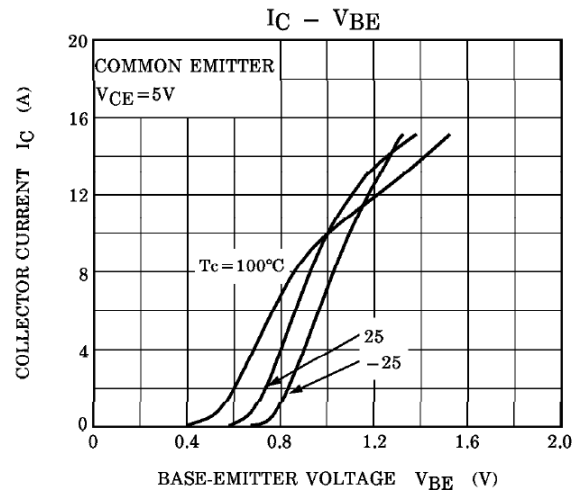
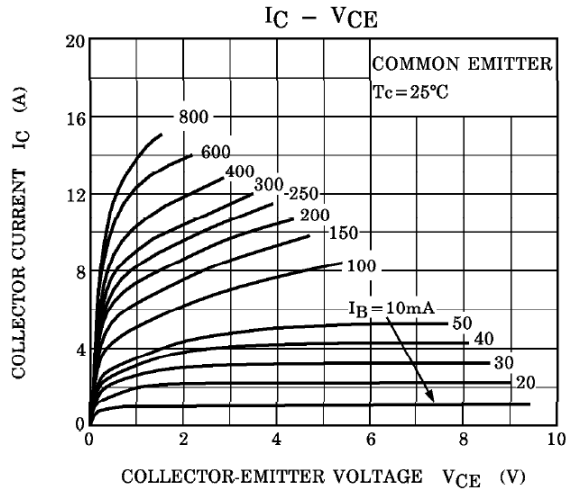
■ h_{FE}(1) Classification

R

O



Typical Characteristics





Package Dimensions

SYMBOL	MILLIMETERS
A (mm)	15.60±0.20
A1 (mm)	13.60±0.20
A2 (mm)	9.60±0.20
B (mm)	19.90±0.20
B1 (mm)	13.90±0.20
B2 (mm)	12.76±0.20
B3 (mm)	3.80±0.20
C (mm)	20.00±0.30
C1 (mm)	3.50±0.20
C2 (mm)	16.50±0.30
D (mm)	5.45 (TYP)
D1 (mm)	2.0±0.20
D2 (mm)	3.0±0.20
D3 (mm)	1.00±0.20
E (mm)	4.80±0.20
E1 (mm)	1.50± ^{+0.15} / _{-0.05}
E2 (mm)	1.40±0.20
F (mm)	18.70±0.20
G (mm)	0.60 ^{+0.15} / _{-0.05}
φ (mm)	3.20±0.10

